

DFN 2×2B-6L P MOS

P-Channel Enhancement Mode Field Effect Transistor in a DFN 2×2B-6L Plastic Package.

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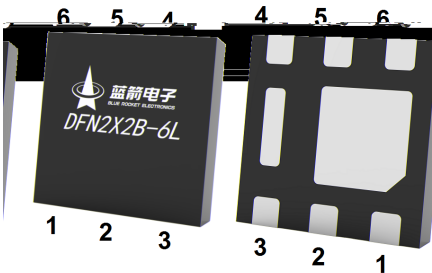
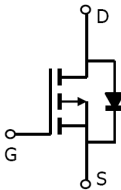
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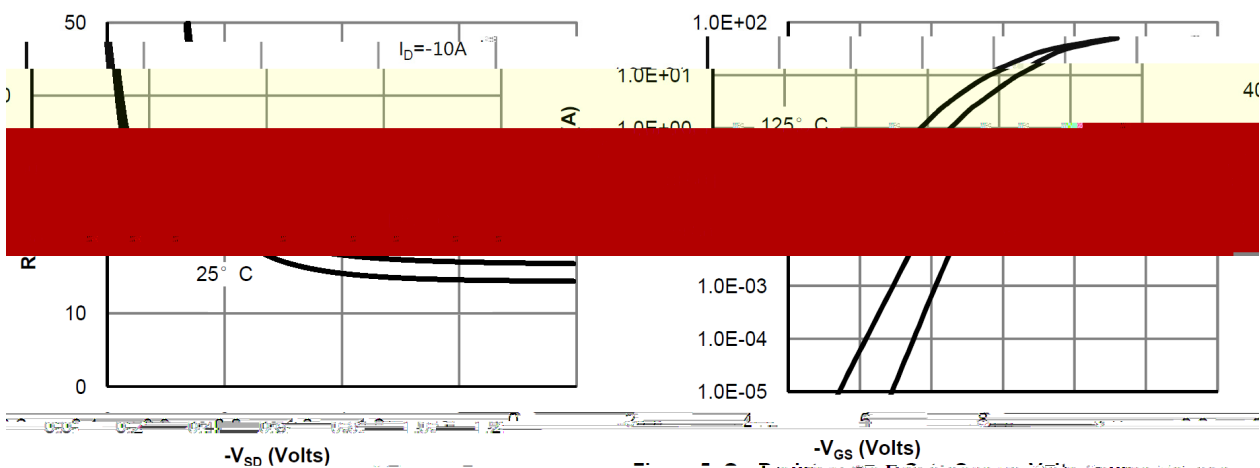
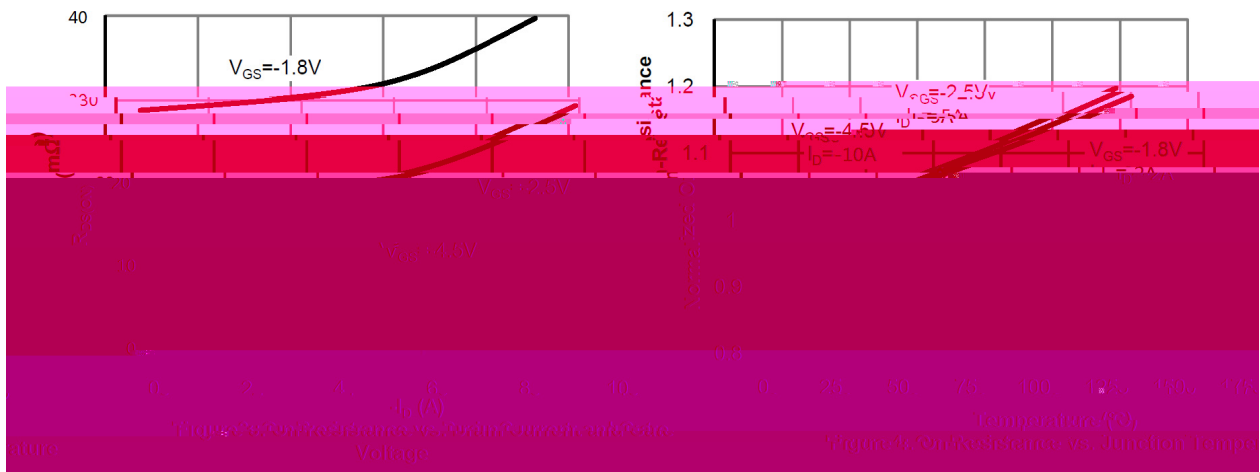
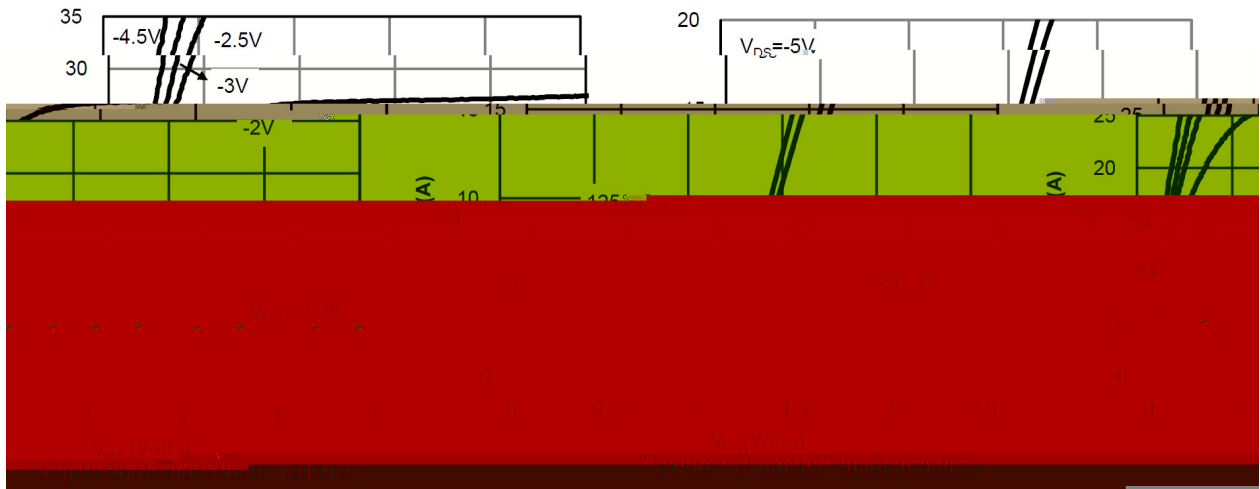


出脚	定义
Pin1	D
Pin2	D
Pin3	G
Pin4	S
Pin5	D
Pin6	D



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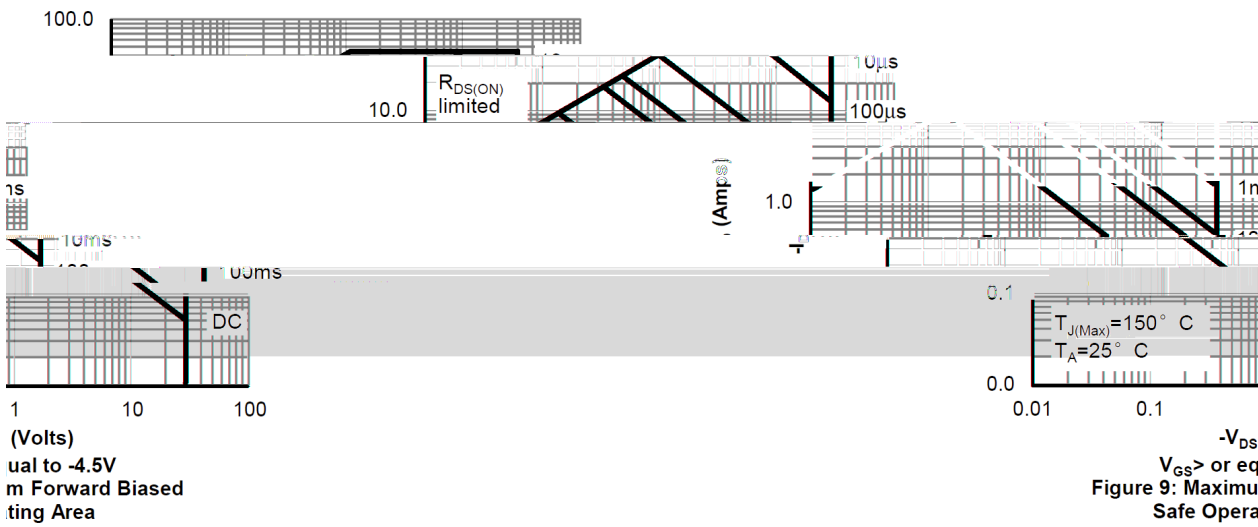
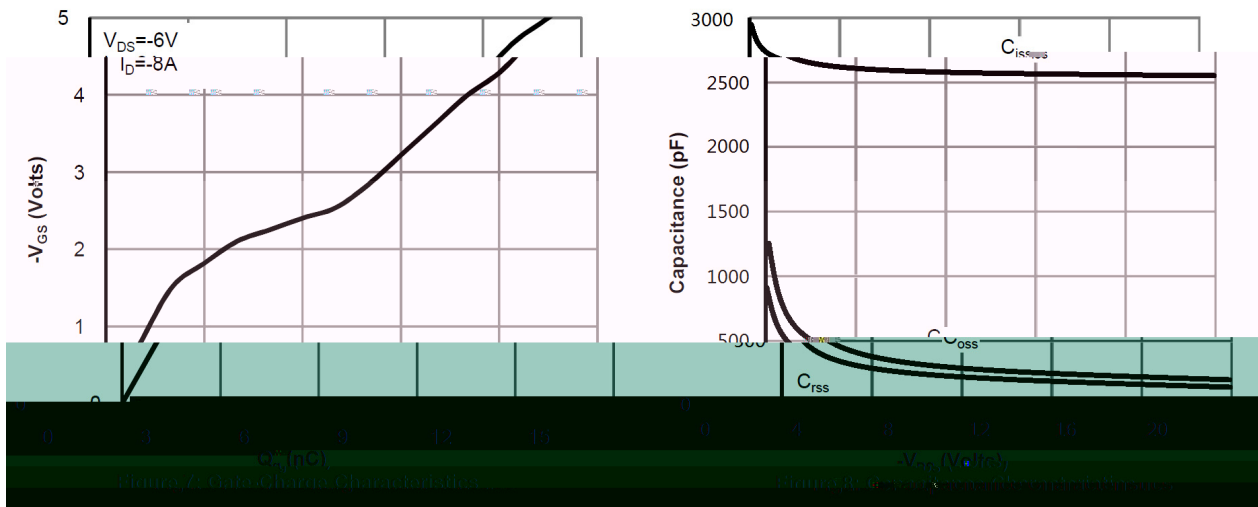
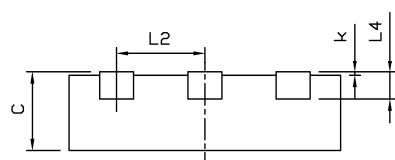
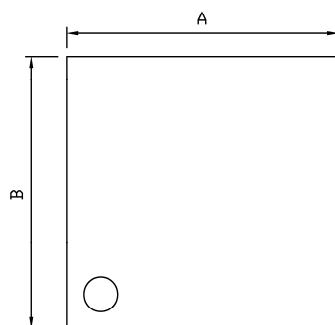
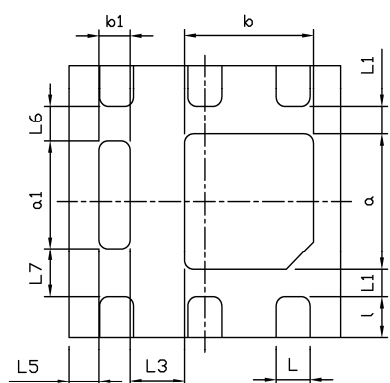


Figure 10: Normalized Maximum Transient Thermal Impedance

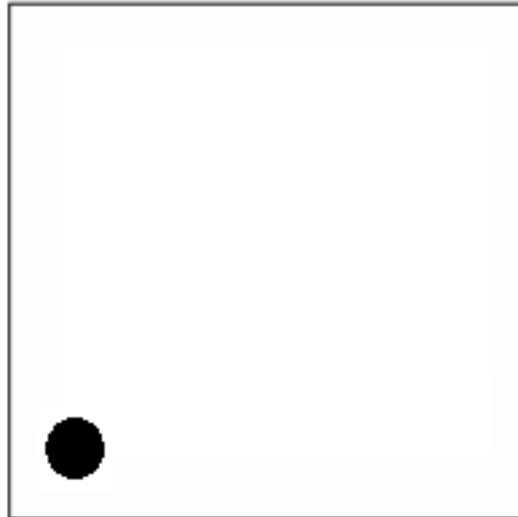
DFN2 X2B-6L-0.5

Unit:mm

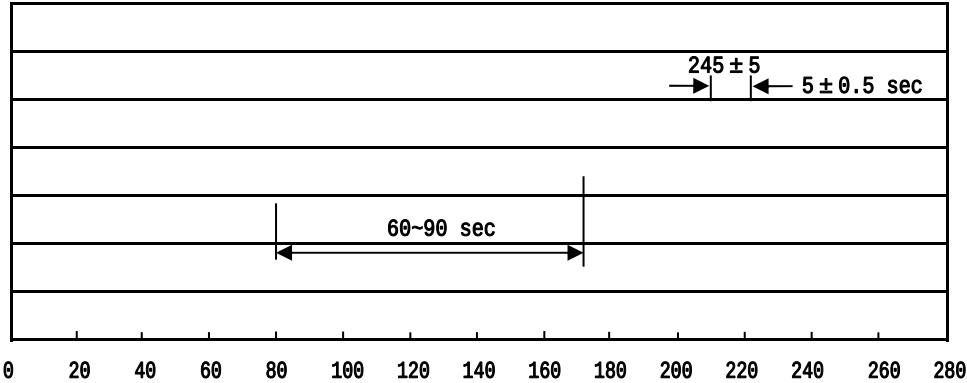


Dimensions In Millimeters			
Symbol	MIN	TYP	MAX
A	1.95	2.00	2.05
B	1.95	2.00	2.05
C	0.45	0.50	0.55
L	0.25	0.30	0.35
L1	0.10	0.20	0.30
L2	-	0.65	-
L3	0.30	0.40	0.50
L4	-	0.152	-
L5	0.12	0.22	0.32
L6	0.15	0.25	0.35
L7	0.23	0.33	0.43
a	0.90	1.00	1.10
a1	0.72	0.82	0.92
b	0.85	0.95	1.05
b1	0.13	0.23	0.33
l	0.25	0.30	0.35
k	0.00	-	0.05

Rev.01 202006



Temperature Profile for IR Reflow Soldering(Pb-Free)



± ± ± ±

± ± °C

	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box